What Is Claimed Is:

1. A method of manufacturing a micromechanical component, the method comprising:

providing a substrate having a front side and a back side; patterning the front side of the substrate;

at least partially covering the patterned front side of the substrate with a protective layer containing germanium;

patterning the back side of the substrate; and at least partially removing the protective layer containing germanium from the patterned front side of the substrate.

- 2. The method according to claim 1, wherein the substrate has a wafer substrate, a first sacrificial layer situated on the wafer substrate and a micromechanical function layer situated on the first sacrificial layer, the micromechanical function layer forming the front side and the wafer substrate forming the back side.
- 3. The method according to claim 1, further comprising forming a hard-surface mask on the front side of the substrate, the protective layer being formed selectively in openings in the hard-surface mask.
- 4. The method according to claim 3, further comprising applying the protective layer to an entire portion of the back side of the substrate.
- 5. The method according to claim 1, further comprising: forming a first hard-surface mask on the front side of the substrate; and forming the protective layer over an entire surface of the first hardsurface mask.
- 6. The method according to claim 5, further comprising forming the protective layer over a nucleation layer over the entire surface.

- 7. The method according to claim 1, further comprising:
 forming a second hard-surface mask on the back side of the substrate;
 and
- etching a cavern into the back side when the front side is covered at least partially by the protective layer.
- 8. The method according to claim 7, further comprising:

 after etching the cavern, removing the protective layer from the front side; and
- subsequently etching trenches in a micromechanical function layer via a first hard-surface mask.
- 9. The method according to claim 7, further comprising forming the second hardsurface mask from the protective layer on the back side.